1051.	1.	c.	4. Checkins of systems for electromagnetic energy storage, containing components manufactured from "superconductive" materials specially designed for operation at temperatures below the "critical temper- ature" of at least one of their "superconductive"	
			<ul> <li>a. Resonant operating frequencies exceeding 1 MHz;</li> <li>b. A stored energy density of 1 MJ/m<sup>3</sup> or more; and</li> </ul>	1031. 2.
1031.	1.	e.	<ul> <li>c. A discharge time of less than 1 ms;</li> <li>5. Flash discharge type X-ray systems, including tubes, having all of the following:</li> <li>a. A peak power exceeding 500 MW;</li> </ul>	
1031	1	f	<ul> <li>b. An output voltage exceeding 500 kV; and</li> <li>c. A pulse width of less than 0.2 microsecond;</li> <li>Rotary input type shaft absolute position encoders having</li> </ul>	1031. 2.
1031.			either of the following: 1. A resolution of better than 1 part in 265,000 (18 bit resolution) of full scale; or	
7903	1 14	1	2. An accuracy better than $\pm$ 2.5 seconds of arc;	1031. 2.
1031. 1031.	2. 2.	Ge a.	Recording equipment, as follows, and specially designed test tape therefor:	
1031.	2.	a.	1. Analogue instrumentation magnetic tape recorders, including those permitting the recording of digital signals (e.g., using a high density digital recording	
			<ul><li>(HDDR) module), having any of the following:</li><li>a. A bandwidth exceeding 4 MHz per electronic channel or track;</li></ul>	1031. 2.
			b. A bandwidth exceeding 2 MHz per electronic channel or track and having more than 42 tracks; or	
1021			c. A time displacement (base) error, measured in accordance with applicable IRIG or EIA documents, of less than $\pm$ 0.1 microsecond;	1032. TE EQUIPN
1031.	2.	a.	2. Digital video magnetic tape recorders having a maximum digital interface transfer rate exceeding 180 Mbit/s, except those specially designed for television recording as standardized or recommended by the	1032. Equ devi com
1031.	2.	a.	<ol> <li>Digital instrumentation magnetic tape data recorders having any of the following characteristics:</li> <li>a A maximum digital interface transfer rate exceed-</li> </ol>	1032. 1.
			<ul> <li>ing 60 Mbit/s and employing helical scan techniques;</li> <li>b. A maximum digital interface transfer rate exceeding 120 Mbit/s and employing fixed head techniques; or</li> <li>c. "Space qualified":</li> </ul>	
			NOTE: 1031.2.a.3 does not embargo analogue magnetic tape recorders equipped with HDDR conversion electronics	1032. 2.
1031.	2.	a.	<ul> <li>and configured to record only digital data.</li> <li>4. Equipment, with a maximum digital interface transfer rate exceeding 60 Mbit/s, designed to convert digital video magnetic tape recorders for use as digital</li> </ul>	
1031.	2.	b.	"Frequency synthesiser" "assemblies" having a "fre- quency switching time" from one selected frequency to	1032. 3.
1031.	2.	c.	another of less than 1 ms; "Signal analysers", as follows: 1. Capable of analysing frequencies exceeding 31 GHz; 2. "Dynamic gingal analysers" with a "real time	
			bandwidth" exceeding 25.6 kHz, except those using only constant percentage bandwidth filters (also known as octave or fractional octave filters);	
1031.	2.	d.	Frequency synthesised signal generators producing output frequencies, the accuracy and short term and long term stability of which are controlled, derived from or disciplined by the internal master frequency, and having any of the following:	1032. 4.
			<ol> <li>A maximum synthesised frequency exceeding 31 GHz;</li> <li>A "frequency switching time" from one selected</li> </ol>	
			frequency to another of less than 1 ms; or 3. A single sideband (SSB) phase noise better than -(126 + 20 log10F - 20 log10f) in dBc/Hz, where E is the	
			off-set from the operating frequency in Hz and f is the operating frequency in MHz;	1032. 5.

## **NOTE:** 1031.2.d. does not embargo equipment in which the output

			frequency is either produced by the addition or subtraction of two or more crystal oscillator frequencies, or by an addition or subtraction followed by a multiplication of the result.
31.	2.	e.	Network analysers with a maximum operating frequency exceeding 31 GHz; NOTE:
			1031.2.e. does not embargo "swept frequency network an- alysers" with a maximum operating frequency not exceed- ing 40 GHz and which do not contain a data bus for remote control interfacing.
31.	2.	f.	Microwave test receivers with both of the following:
			and
			2. Capable of measuring amplitude and phase simulta- neously;
31.	2.	g.	Atomic frequency standards having either of the following characteristics:
			1. Long term stability (aging) less (better) than 1 x 10 <sup>-11</sup> /month; or
			2. "Space qualified";
			1031.2.g.1. does not embargo non-"space qualified" rubid- ium standards.
31.	2.	h.	Emulators for microcircuits embargoed by 1031.1.a.3. or 1031.1.a.9.
			NOTE: 1031.2.h. does not embargo emulators designed for a "fam- ily" which contains at least one device not embargoed by 1031.1.a.3. or 1031.1.a.9.

## 1032. TEST, INSPECTION AND PRODUCTION EQUIPMENT

1032.	Equipment for the manufacture or testing of semiconductor devices or materials, as follows, and specially designed components and accessories therefor:
1032.	<ol> <li>"Stored programme controlled" equipment for epitaxial growth, as follows:</li> <li>a. Capable of producing a layer thickness uniform to less than ± 2.5% across a distance of 75 mm or more;</li> </ol>
	<ul> <li>b. Metal organic chemical vapour deposition (MOCVD) reactors specially designed for compound semiconductor crystal growth by the chemical reaction between materials embargoed by 1033.3 or 1033.4;</li> <li>c. Molecular beam epitaxial growth equipment using gas</li> </ul>
1032.	<ul><li>sources;</li><li>2. "Stored programme controlled" equipment designed for ion implantation, having any of the following:</li></ul>
	<ul> <li>a. An accelerating voltage exceeding 200 keV;</li> <li>b. Specially designed and optimized to operate at an accelerating voltage of less than 10 keV;</li> <li>c. Direct write capability: or</li> </ul>
	<ul> <li>d. Capable of high energy oxygen implant into a heated semiconductor material "substrate";</li> </ul>
1032.	3. "Stored programme controlled" anisotropic plasma dry etching equipment, as follows:
	a. With cassette-to-cassette operation and load-locks, and having either of the following:
	1. Magnetic confinement; or
	2. Electron cyclotron resonance (ECK);
	b. Specially designed for equipment embargoed by 1032.6. and having either of the following:
	1. Magnetic confinement; or
1000	2. Electron cyclotron resonance (ECR);
1032.	4. "Stored programme controlled" plasma enhanced CVD
	equipment, as follows:
	a. with casselle-to-casselle operation and load-locks, and
	1 Magnetic confinement: or
	2 Electron cyclotron resonance (ECP):
	<ul> <li>b. Specially designed for equipment embargoed by 1032.6. and having either of the following:</li> </ul>
	1. Magnetic confinement; or
	2. Electron cyclotron resonance (ECR):
1032.	5. "Stored programme controlled" multifunctional focussed ion
	beam systems specially designed for manufacturing, repair-